



AWB7031

2.01 to 2.025 GHz

Small-Cell Power Amplifier Module
ADVANCED PRODUCT INFORMATION - Rev 0.1

FEATURES

- InGaP HBT Technology
- -47 dBc ACPR @ ± 10 MHz, +24.5 dBm
- 30 dB Gain
- High Efficiency
- Low Transistor Junction Temperature
- Internally matched for a 50 Ω System
- Low Profile Miniature Surface Mount Package; Halogen Free and RoHS Compliant
- Multi-Carrier Capability

APPLICATIONS

- LTE, WCDMA and HSDPA Air Interfaces
- FDD and TDD Systems
- Picocell, Femtocell, Home Nodes
- Customer Premises Equipment (CPE)
- Data Cards and Terminals



**14 Pin 5 mm x 5 mm x 1 mm
Surface Mount Module**

PRODUCT DESCRIPTION

The AWB7031 is a highly linear, fully matched, power amplifier module designed for picocell, femtocell, and customer premises equipment (CPE) applications. Its high power efficiency and low adjacent channel power levels meet the extremely demanding needs of small cell infrastructure architectures. Designed for LTE, WCDMA, HSDPA air interfaces operating in the 2.01 GHz to 2.025 GHz band, the AWB7031 delivers up to

+24.5 dBm of LTE (E-TM1.1) power with an ACPR of -47 dBc. It operates from a convenient +4.2 V supply and provides 30 dB of gain. The device is manufactured using an advanced InGaP HBT MMIC technology offering state-of-the-art reliability, temperature stability, and ruggedness. The self-contained 5 mm x 5 mm x 1 mm surface mount package incorporates RF matching networks optimized for output power, efficiency, and linearity in a 50 Ω system.

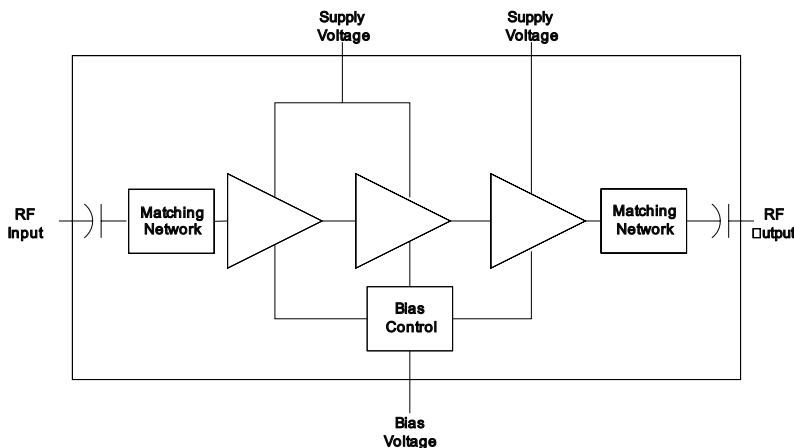


Figure 1: Block Diagram

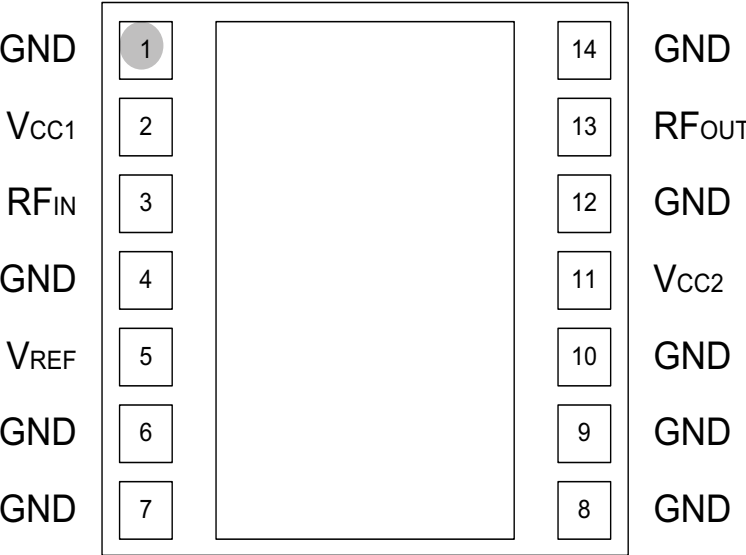


Figure 2: Pinout (X-ray Top View)

Table 1: Pin Description

PIN	NAME	DESCRIPTION
1	GND	Ground
2	V _{CC1}	Supply Voltage
3	RF _{IN}	RF Input
4	GND	Ground
5	V _{REF}	Reference Voltage
6	GND	Ground
7	GND	Ground
8	GND	Ground
9	GND	Ground
10	GND	Ground
11	V _{CC2}	Supply Voltage
12	GND	Ground
13	RF _{OUT}	RF Output
14	GND	Ground

ELECTRICAL CHARACTERISTICS

Table 2: Absolute Minimum and Maximum Ratings

PARAMETER	MIN	MAX	UNIT
Supply Voltage (V_{CC})	0	+5	V
Reference Voltage (V_{REF})	0	+3.5	V
RF Output Power (P_{OUT})	-	+28	dBm
Storage Temperature (T_{STG})	-40	+150	°C

Stresses in excess of the absolute ratings may cause permanent damage. Functional operation is not implied under these conditions. Exposure to absolute ratings for extended periods of time may adversely affect reliability.

Table 3: Operating Ranges

PARAMETER	MIN	TYP	MAX	UNIT	COMMENTS
Operating Frequency (f)	2010	-	2025	MHz	
Supply Voltage (V_{CC})	+3.2	+4.2	+4.5	V	
Reference Voltage (V_{REF})	+2.80 0	+2.85 -	+2.90 +0.5	V	PA "on" PA "shut down"
RF Output Power (P_{OUT})	-	+24.5	-	dBm	
Case Temperature (T_C)	-40	-	+85	°C	

The device may be operated safely over these conditions; however, parametric performance is guaranteed only over the conditions defined in the electrical specifications.

Table 4: Electrical Specifications
($T_C = +25\text{ }^\circ\text{C}$, $V_{CC} = +4.2\text{ V}$, $V_{REF} = +2.85\text{ V}$, $50\text{ }\Omega$ system)

PARAMETER	MIN	TYP	MAX	UNIT	COMMENTS
Gain ⁽²⁾	-	30	-	dB	
ACPR ^{(1), (2), (3)} @ 10 MHz @ 20 MHz	- -	-47 -58	- -	dBc	
Power-Added Efficiency ^{(1), (2), (3)}	-	17	-	%	
Thermal Resistance (R_{JC})	-	TBD	-	$^\circ\text{C/W}$	Junction to Case
Supply Current ^{(1), (2), (3)}	-	395	-	mA	total through V_{CC} pins
Quiescent Current (I_{cq})	-	130	-	mA	
Reference Current	-	8	-	mA	through V_{REF} pin
Leakage Current	-	1.5	-	μA	$V_{CC} = +4.5\text{ V}$, $V_{REF} = 0\text{ V}$
Harmonics 2fo 3fo, 4fo	- -	-50 -60	- -	dBc	
Input Return Loss	-	13	-	dB	
P1dB	-	TBD	-	dBm	CW tone
RF Switching Time ⁽⁴⁾ Rise Time (PA “off” to “on”) Fall Time (PA “on” to “off”)	- -	- -	12 4	μs	$V_{CC} = +4.2$, V_{REF} switched between 0 V and +2.85 V
Spurious Output Level (all spurious outputs)	-	-	-60	dBc	$P_{OUT} \leq +24.5\text{ dBm}$ In-band load VSWR < 5:1 Out-of-band load VSWR < 10:1 Applies over all voltage and temperature operating ranges
Load mismatch stress with no permanent degradation or failure	8:1	-	-	VSWR	$V_{CC} = +4.2\text{ V}$, $P_{IN} = 0\text{ dBm}$ Applies over full operating temperature range

Notes:

(1) Measured at 2017.5 MHz.

(2) $P_{OUT} = +24.5\text{ dBm}$.

(3) E-TM1.1 LTE 10 MHz BW.

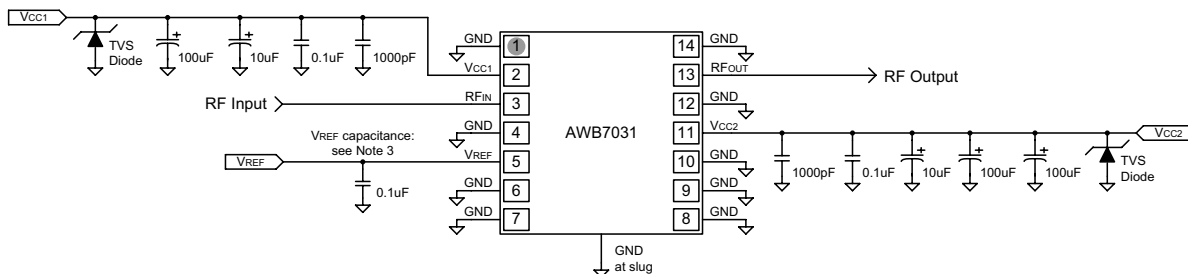
(4) Rise Time defined from time at which V_{REF} is switched from 0 V to +2.85 V, to time at which the RF output power achieves 90% of the average steady-state “on” level; Fall Time defined from time at which V_{REF} is switched from +2.85 V to 0 V, to time at which the RF output power decreases to 10% of the average steady-state “on” level.

APPLICATION INFORMATION

To ensure proper performance, refer to all related Application Notes on the ANADIGICS web site:
<http://www.anadigics.com>

Shutdown Mode

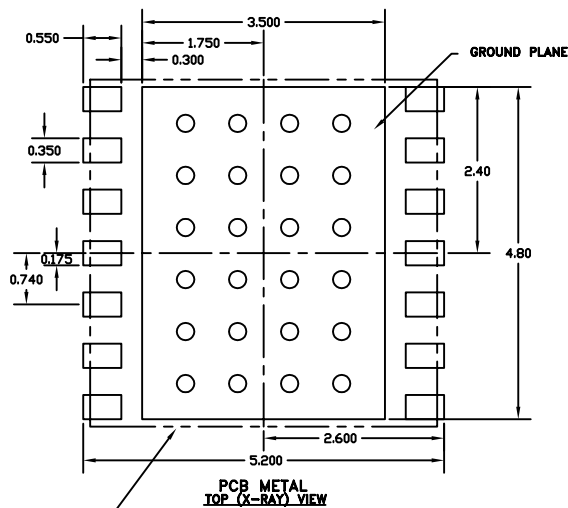
The power amplifier may be placed in a shutdown mode by applying logic low levels (see Operating Ranges table) to the V_{REF} voltage.



Notes:

1. 10uF and 100uF capacitors are optional.
2. Applications that have large supply voltage transients may benefit from the use of TVS diodes. For such applications, recommended TVS diodes are SM05T1G or SMJ5.0A.
3. To achieve the RF Switching Time specifications listed in Table 4, the maximum recommended capacitance on the V_{REF} line is 0.01uF. The noise on the V_{REF} line should be kept as low as possible to minimize required capacitance.

Figure 3: Application Circuit Schematic

**NOTES:**

- (1) OUTLINE DRAWING REFERENCE:
P8002543
- (2) UNLESS SPECIFIED DIMENSIONS
ARE SYMMETRICAL ABOUT CENTER
LINES SHOWN.
- (3) DIMENSIONS IN MILLIMETERS.
- (4) VIAS SHOWN IN PCB METAL VIEW
ARE FOR REFERENCE ONLY.
NUMBER & SIZE OF THERMAL VIAS
REQUIRED DEPENDENT ON HEAT
DISSIPATION REQUIREMENT AND THE
PCB PROCESS CAPABILITY.
- (5) RECOMMENDED STENCIL THICKNESS:
APPROX. 0.125mm (5 Mils)

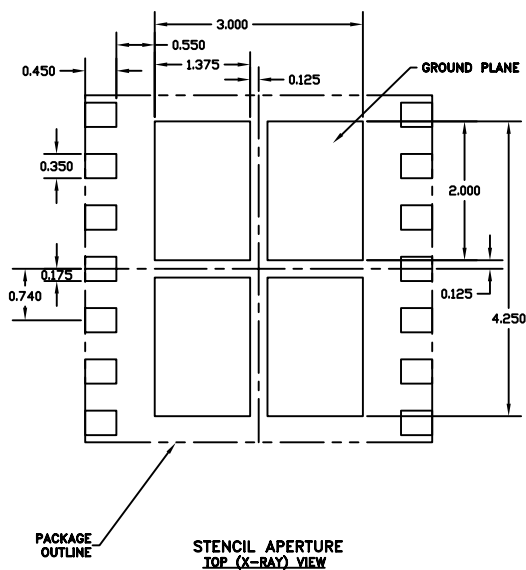
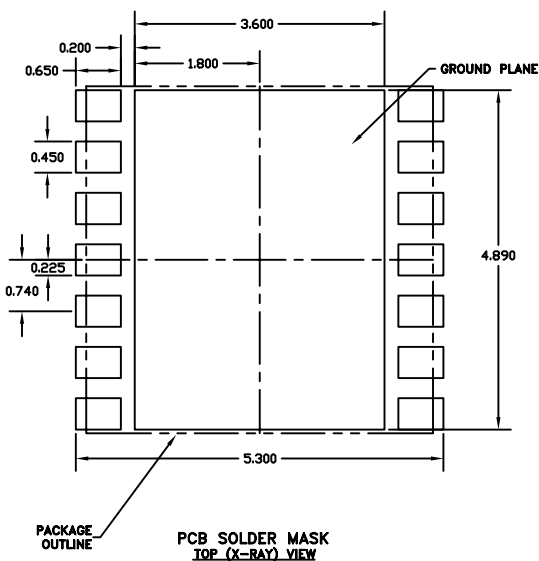
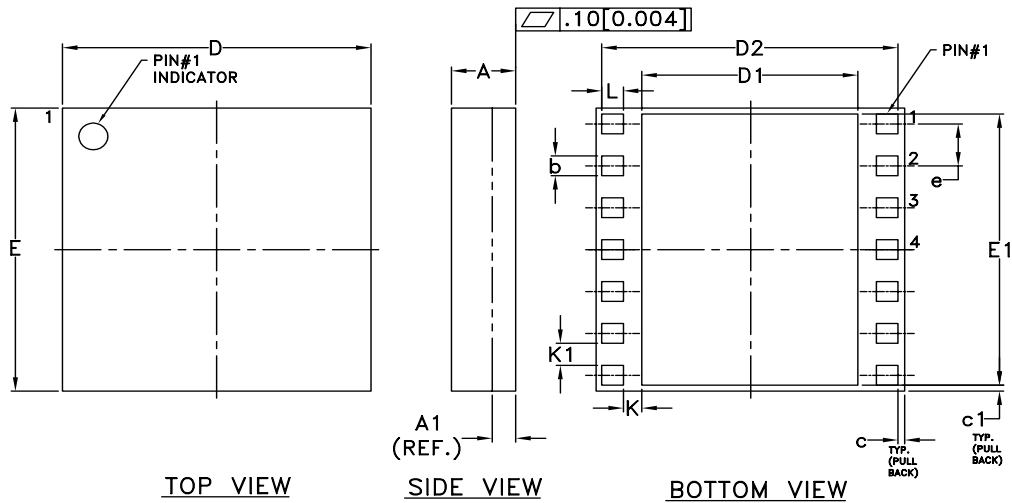


Figure 4: PCB Footprint

PACKAGE OUTLINE



- NOTES:
- 1. CONTROLLING DIMENSIONS: MILLIMETERS
 - 2. UNLESS SPECIFIED TOLERANCE=±0.076[0.003].
 - 3. PADS (INCLUDING CENTER) SHOWN UNIFORM SIZE FOR REFERENCE ONLY. ACTUAL PAD SIZE AND LOCATION WILL VARY WITHIN MIN. AND MAX. DIMENSIONS ACCORDING TO SPECIFIC LAMINATE DESIGN.
 - 4. METAL PAD DIMENSION IS MEASURED AT THE BOTTOM OF THE METAL LAYER.

S _W 60L	MILLIMETERS			INCHES			NOTE
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
A	0.88	0.98	1.08	0.035	0.039	0.043	—
A1	0.32			0.013			—
b	0.33	0.35	0.38	0.013	0.014	0.015	—
c	—	0.10	—	—	0.004	—	—
c1	—	0.10	—	—	0.004	—	—
D	4.90	5.00	5.10	0.193	0.197	0.201	—
D1	3.45	3.50	3.55	0.136	0.138	0.140	—
D2	4.75	4.80	4.85	0.187	0.189	0.191	—
E	4.90	5.00	5.10	0.193	0.197	0.201	—
E1	4.75	4.80	4.85	0.187	0.189	0.191	—
e	0.74			0.029			—
K	0.25	0.30	0.35	0.010	0.012	0.014	—
K1	0.34	0.39	0.44	0.013	0.015	0.017	—
L	0.33	0.35	0.38	0.013	0.014	0.015	—

Figure 5: Package Outline - 14 Pin 5 mm x 5 mm x 1 mm Surface Mount Module

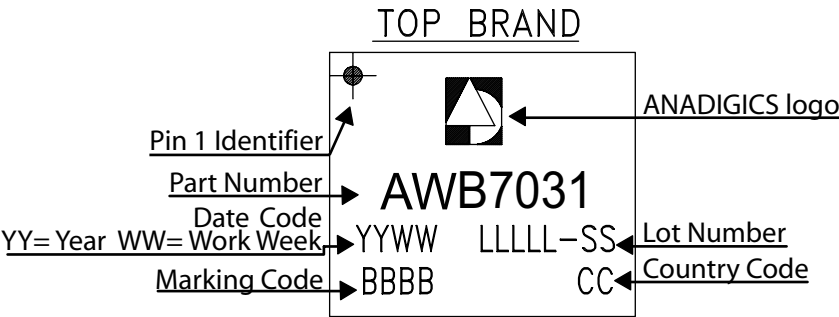


Figure 6: Branding Specification



ANADIGICS

141 Mount Bethel Road
Warren, New Jersey 07059, U.S.A.
Tel: +1 (908) 668-5000
Fax: +1 (908) 668-5132

URL: <http://www.anadigics.com>

IMPORTANT NOTICE

ANADIGICS, Inc. reserves the right to make changes to its products or to discontinue any product at any time without notice. The product specifications contained in Advanced Product Information sheets and Preliminary Data Sheets are subject to change prior to a product's formal introduction. Information in Data Sheets have been carefully checked and are assumed to be reliable; however, ANADIGICS assumes no responsibilities for inaccuracies. ANADIGICS strongly urges customers to verify that the information they are using is current before placing orders.

WARNING

ANADIGICS products are not intended for use in life support appliances, devices or systems. Use of an ANADIGICS product in any such application without written consent is prohibited.